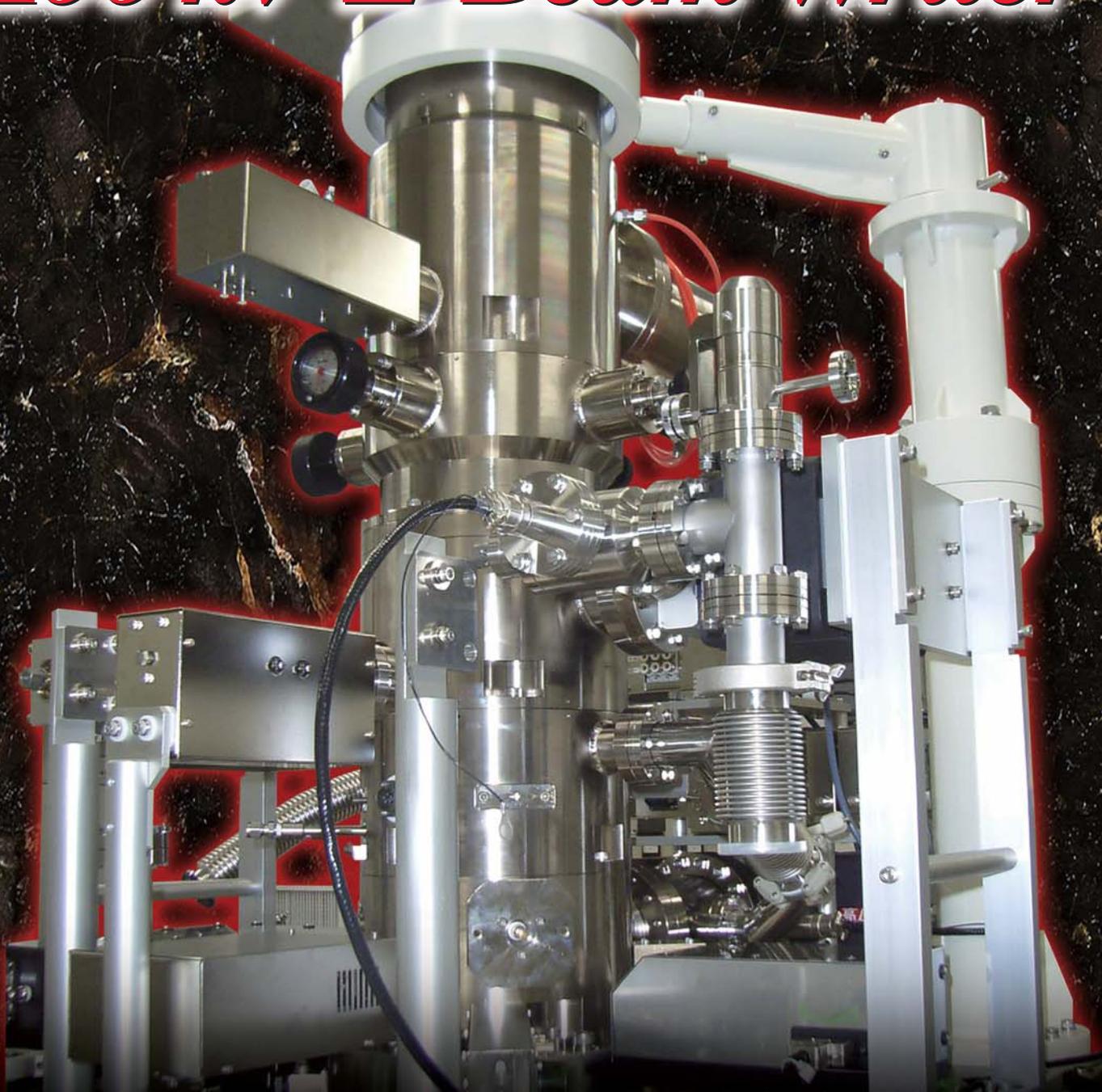


High Voltage Electron Beam Column for 100 kV E-Beam Writer



Electron Column

Electron Source..... ZrO/W
Beam Energy..... 50, 100 keV
Beam Shape..... Gaussian Spot Beam
Beam Current..... Up to 100 nA
Imaging Area..... 500 μm ~ 0.5 μm
Min. Line Width..... 10 nm at 5 nA, 100 kV
Electron Optics..... 3-lens Optics
Emitter Protection .. Built-in

Beam Blanker and Amplifier

(Optional unit for EB recorder and writer)
Rise-up and Fall-down... <4 nsec
Repetition Frequency... >30 MHz

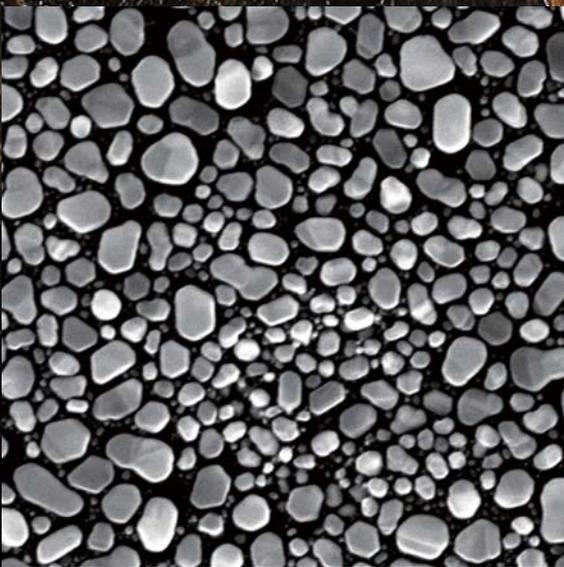
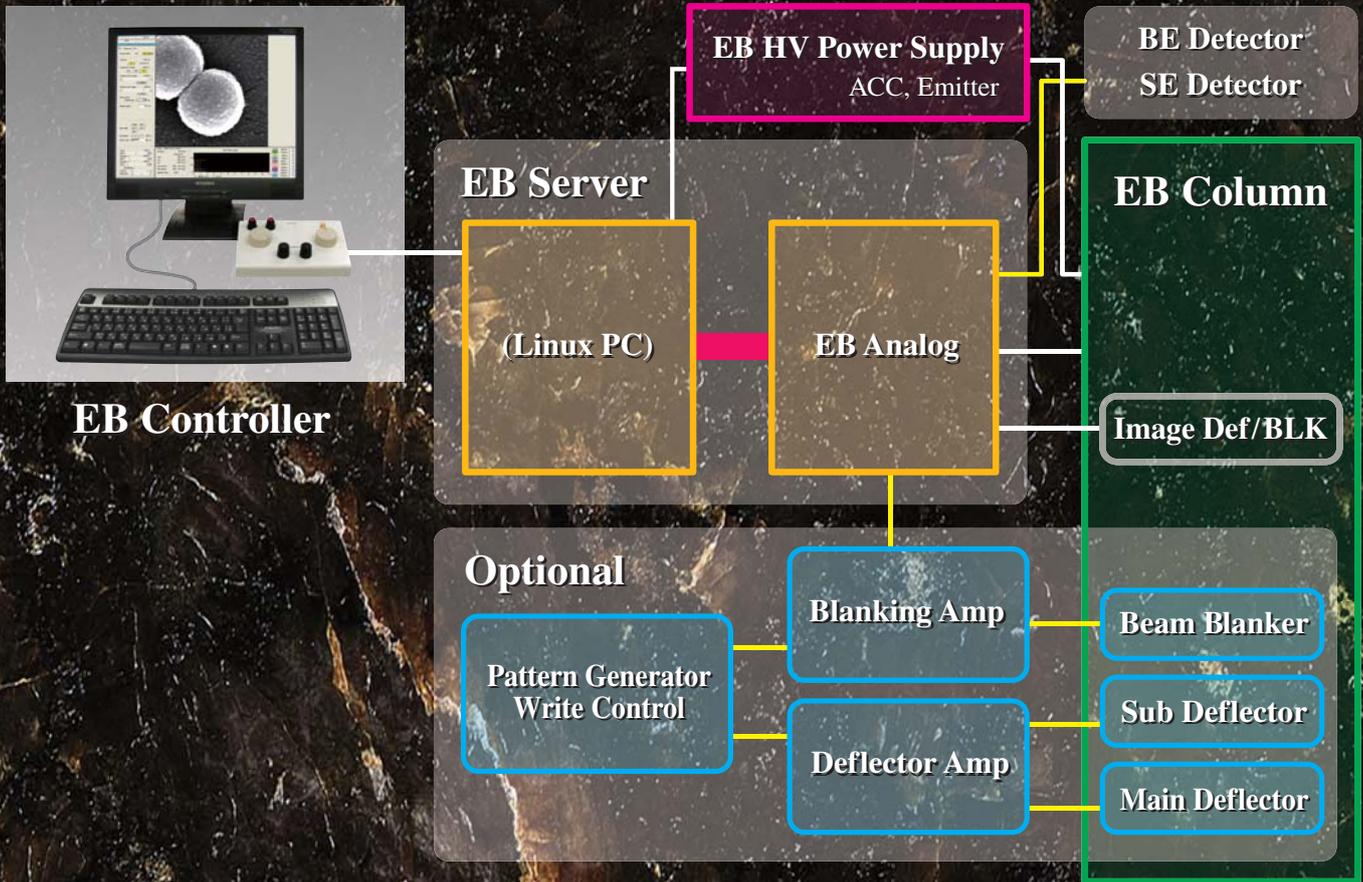
Deflection Units and Amplifiers

(Optional unit for EB writer)
Main Deflection..... 20 bit \leq 500 nsec (FS/32)
Sub Deflection..... 14 bit \leq 40 nsec (FS/4)

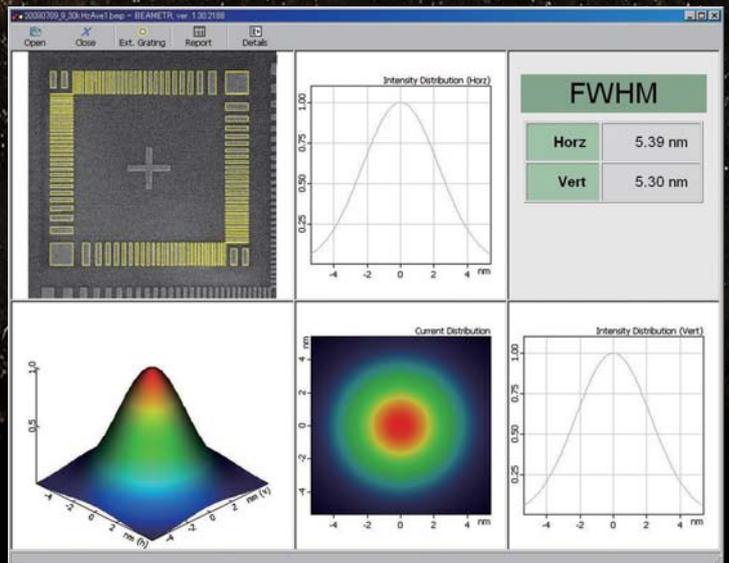
Specifications are subject to change without notice.
Contents of this catalog last updated April 2004.

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<http://www.aandd.jp>

Finer Electron Beam with Larger Beam Current



Field of View 3 μm
SE Image of Gold on Carbon Sample
with 20 nA, 100 keV Beam



Beam Diameter Examination
by BEAMETR™ with 20.0 nA, 100 keV
Beam Diameter(FWHM) ≤ 6 nm

BEAMETR is a trademark of Abeam Technologies, Inc.